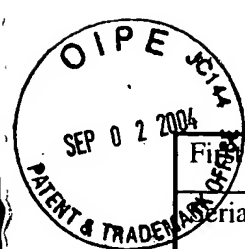


First Named Inventor	Leonard Forbes	<b>GENERAL TRANSMITTAL FORM UNDER 37 CFR 1.8 (LARGE ENTITY)</b>
Serial No.	10/775,908	
Filing Date	February 10, 2004	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	1212	
Attorney Docket No.	400.272US01	
Title: NROM FLASH MEMORY WITH A HIGH-PERMITTIVITY GATE DIELECTRIC		

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Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

<b>Enclosures</b>					
<b>The following documents are enclosed:</b>					
<input checked="" type="checkbox"/>	Information Disclosure Statement (1 pg.); Form 1449 (7 pgs.); 58 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);				
<input checked="" type="checkbox"/>	An itemized return-receipt postcard				
Leffert Jay & Polglaze, P.A. P.O. Box 581009 Minneapolis, MN 55458-1009 T - 612/312-2200 F - 612/312-2250					
<b>Please charge any additional fees or credit any overpayments to Deposit Account No. 501373.</b>					
<b>CUSTOMER NO. 27073</b>					
<b>Submitted By</b>					
Name	Kenneth W. Bolvin	Reg. No.	34,125	Telephone	(612) 312-2211
Signature				Date	8/31/04
<b>Certificate of Mailing</b>					
I certify that this correspondence and the identified documents listed on this transmittal are being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop: AMENDMENT, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on August 31, 2004.					
Name	Rhonda L. Foley		Signature		

(LARGE ENTITY TRANSMITTAL UNDER 37 CFR § 1.8)



Filed Named Inventor	Leonard Forbes	<b>INFORMATION DISCLOSURE STATEMENT</b>
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In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application.

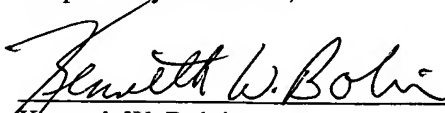
Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.

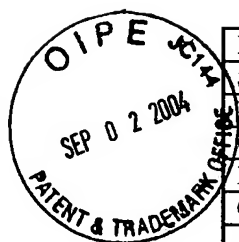
If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Respectfully submitted,

Date: 8/31/04

  
Kenneth W. Bolvin  
Reg. No. 34,125

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Examiner Initials	Foreign Patent		Name	Publication Date	Translation
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Title: NROM FLASH MEMORY WITH HIGH-PERMITTIVITY GATE DIELECTRIC		Sheet 7 of 7

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	H. Tomiye, et al., "A novel 2-bit/cell MONOS memory device with a wrapped-control-gate structure that applies source-side hot-electron injection," 2002 Symposium on VLSI Technology Digest of Technical Papers, Copyright 2002 IEEE.
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Examiner Signature		Date Considered	
<p><small>*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small></p>			